

ABSTRACT OF THE DISCLOSURE

While supplying DHF as a chemical liquid to wafers W each having a resist pattern formed on the surface, oxidation films on the wafers W are eliminated by etching and 5 successively, the surfaces of the wafers W are cleaned by supplying the wafers W with a rinsing liquid. Subsequently, by supplying an ozone water of a predetermined concentration, oxidation films are formed on the wafers W in order to make their surfaces hydrophilic. Then, N₂-gas (dry gas) is 10 supplied to the wafers W in order to remove moisture adhering to the surfaces of the wafers W. In this way, it is possible to prevent an occurrence of water-marks on the wafers W without collapsing the resist patterns formed on the wafers W, 15 allowing both quality and yield rate of the wafers to be improved.

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